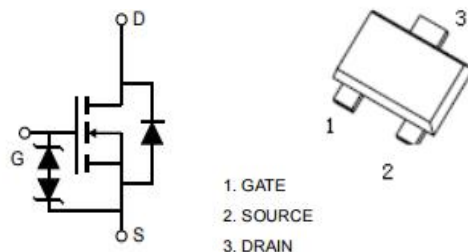


**SOT-723 30V N Channel Enhancement ESD Protection 沟道增强型带静电保护
MOS Field Effect Transistor 场效应管**



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 12	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	0.7	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	1.8	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	150	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	850	$^\circ C/W$
ESD Protected Up to 人体模式静电保护范围	ESD(HBM)	2.0	kV
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ **Device Marking 产品字标**

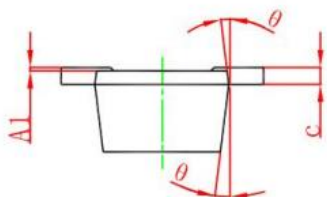
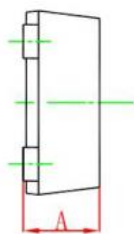
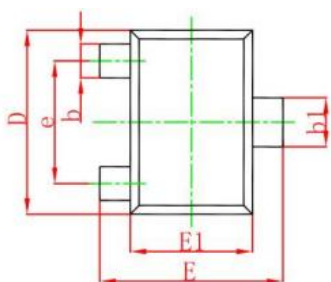
FS3144KT7=KM

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压($I_D=250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	30	—	—	V
Gate Threshold Voltage 栅极开启电压($I_D=250\mu\text{A}, V_{GS}=V_{DS}$)	$V_{GS(th)}$	0.6	0.95	1.3	V
Zero Gate Voltage Drain Current 零栅压漏极电流($V_{GS}=0\text{V}, V_{DS}=30\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流($V_{GS}=\pm 12\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 10	μA
Static Drain-Source On-State Resistance 静态漏源导通电阻($I_D=0.5\text{A}, V_{GS}=4.5\text{V}$) ($I_D=0.5\text{A}, V_{GS}=2.5\text{V}$)	$R_{DS(ON)}$	—	350 450	420 560	$\text{m}\Omega$
Diode Forward Voltage Drop 内附二极管正向压降($I_{SD}=0.7\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1	V

■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimet	
	Min	Max
A	0.40	0.50
A1	0.00	0.10
b	0.15	0.25
b1	0.20	0.30
c	0.06	0.16
D	1.10	1.30
e	0.8TYP	
E	1.10	1.30
E1	0.70	0.90
θ	8°	10°